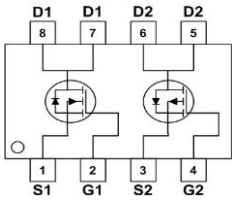
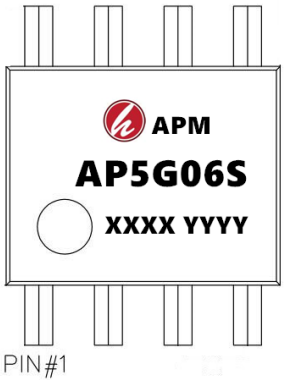
AP5G06S

60V N+P-Channel Enhancement Mode MOSFET

Description



The AP5G06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = 60V I_D =4.8 A

$R_{DS(ON)}$ < 32mΩ @ V_{GS}=10V

V_{DS} = -60V I_D =-3.7 A

$R_{DS(ON)}$ < 70mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP5G06S	SOP-8	AP5G06S XXXX YYYY	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	60	-60	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	4.8	-3.7	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	3.8	-3	A
I_{DM}	Pulsed Drain Current[2]	9.6	-7.5	A
EAS	Single Pulse Avalanche Energy[3]	25.5	35.3	mJ
I_{AS}	Avalanche Current	22.6	-26.6	A
P_D@T_A=25℃	Total Power Dissipation[4]	1.5	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	85	℃/W

$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	36	℃/W

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.063	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=4A	---	---	32	mΩ
		V_{GS}=4.5V , I_D=2A	---	---	38	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.24	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=4A	---	21	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.2	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=48V , V_{GS}=4.5V , I_D=4A	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	6.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3 , I_D=4A	---	8	---	ns
T_r	Rise Time		---	14.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.4	---	
T_f	Fall Time		---	4.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1378	---	pF
C_{oss}	Output Capacitance		---	86	---	
C_{rss}	Reverse Transfer Capacitance		---	64	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	4.8	A
I_{SM}	Pulsed Source Current[2,5]		---	---	9.6	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is VDD=-25V,VGS=-10V,L=0.1mH,IAS=-26.6A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.03	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-3A	---	---	70	mΩ
		V_{GS}=-4.5V , I_D=-2A	---	---	105	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	---	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.56	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-3A	---	15	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	13.5	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-48V , V_{GS}=-4.5V , I_D=-3A	---	9.86	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	
Q_{gd}	Gate-Drain Charge		---	2.95	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3 , I_D=-1A	---	28.8	---	ns
T_r	Rise Time		---	19.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	60.8	---	
T_f	Fall Time		---	7.2	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	1447	---	pF
C_{oss}	Output Capacitance		---	97.3	---	
C_{rss}	Reverse Transfer Capacitance		---	70	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-3.7	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-7.5	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=22.6A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation

N-Channel Typical Characteristics

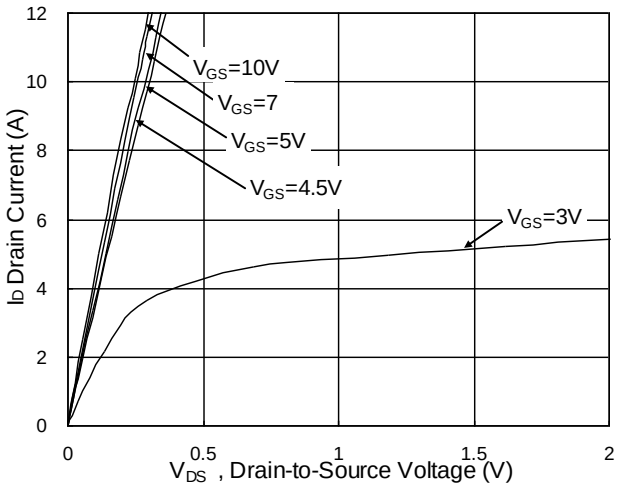


Fig.1 Typical Output Characteristics

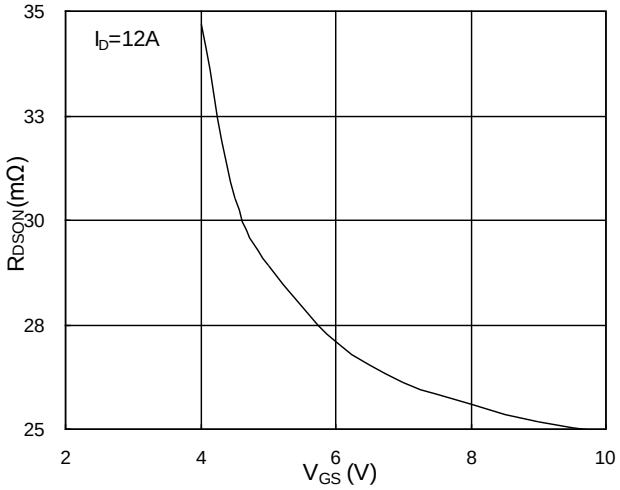


Fig.2 On-Resistance v.s Gate-Source

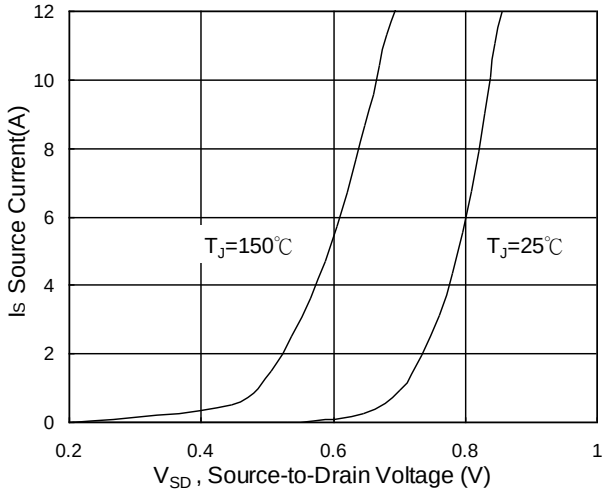


Fig.3 Forward Characteristics of Reverse

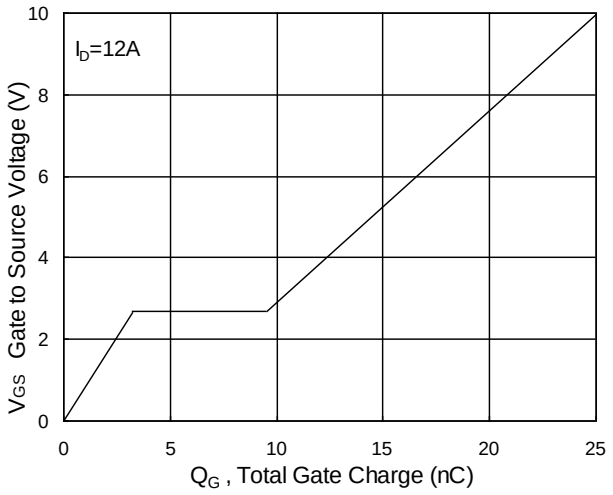


Fig.4 Gate-Charge Characteristics

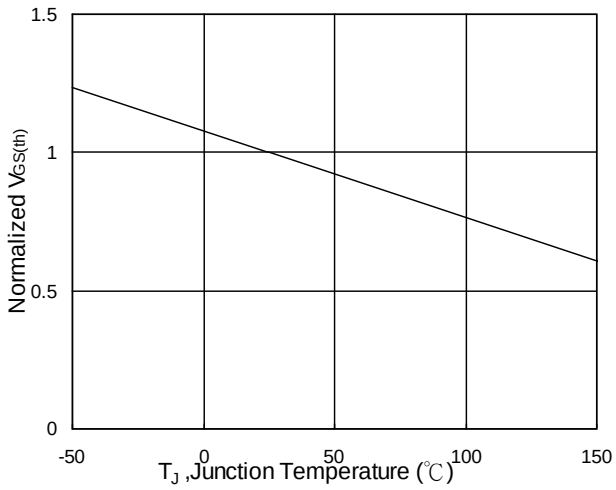


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

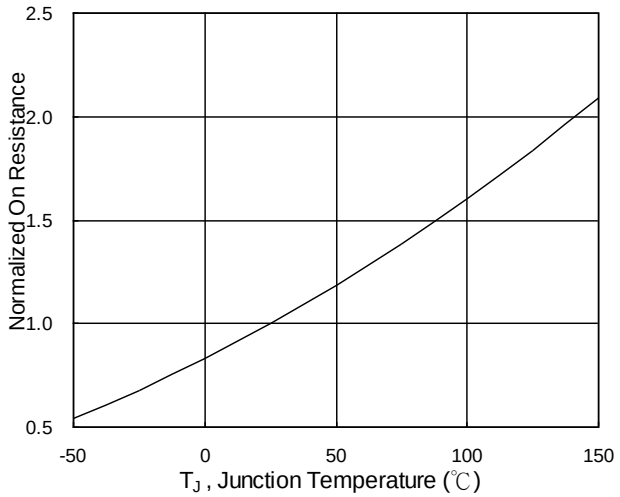


Fig.6 Normalized R_{DSON} v.s T_J

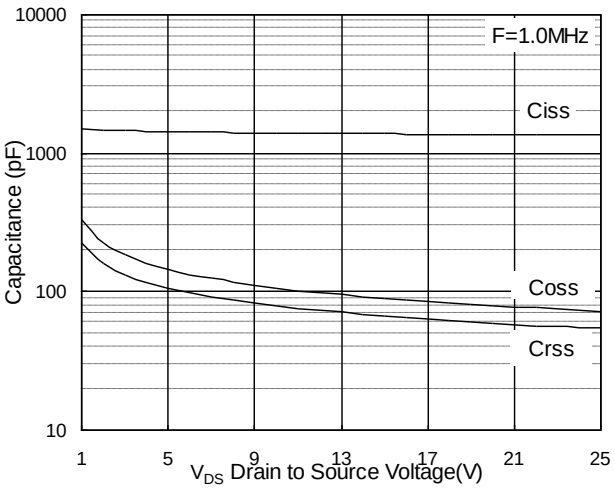


Fig.7 Capacitance

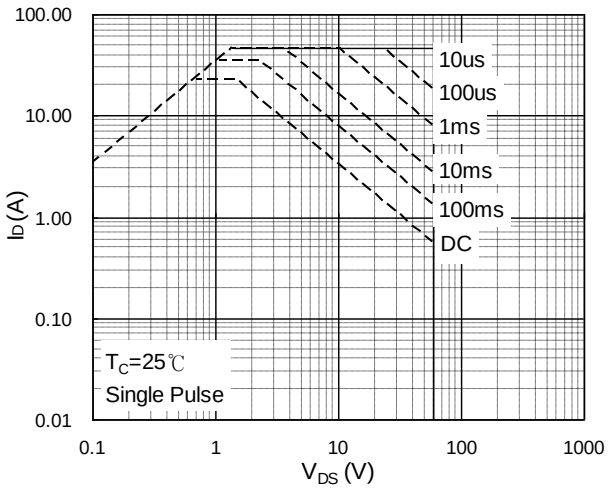


Fig.8 Safe Operating Area

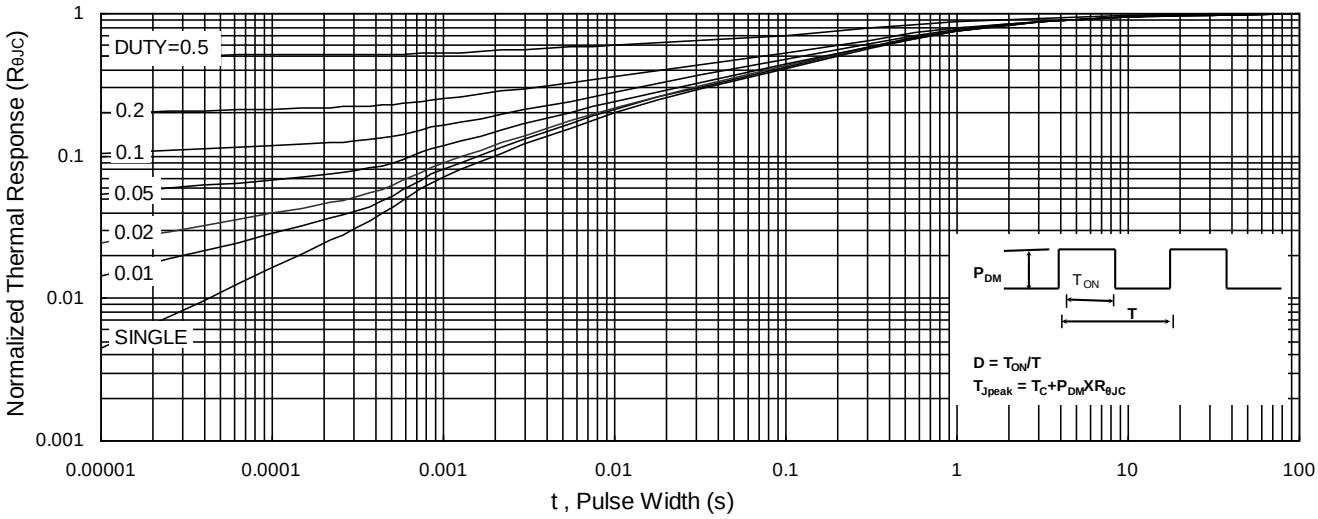


Fig.9 Normalized Maximum Transient Thermal Impedance

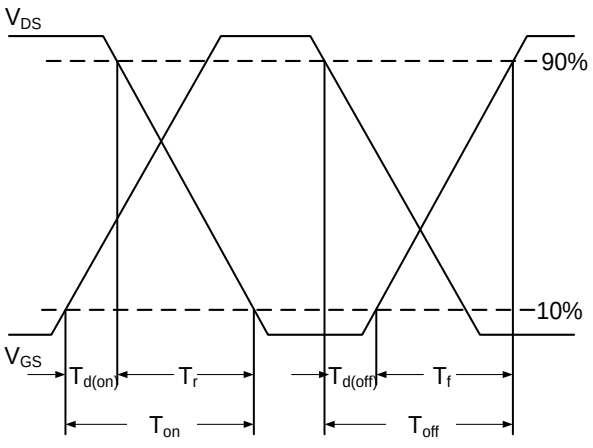


Fig.10 Switching Time Waveform

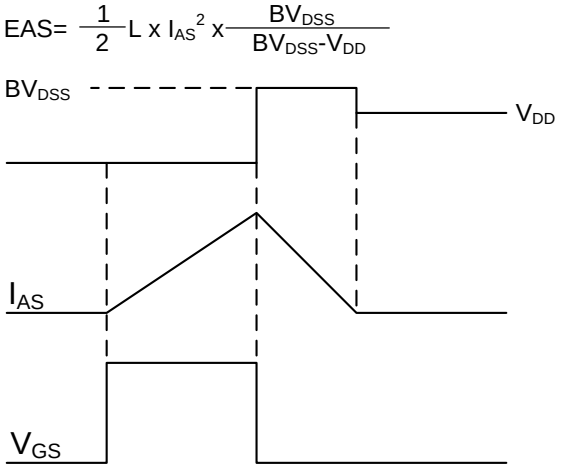


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

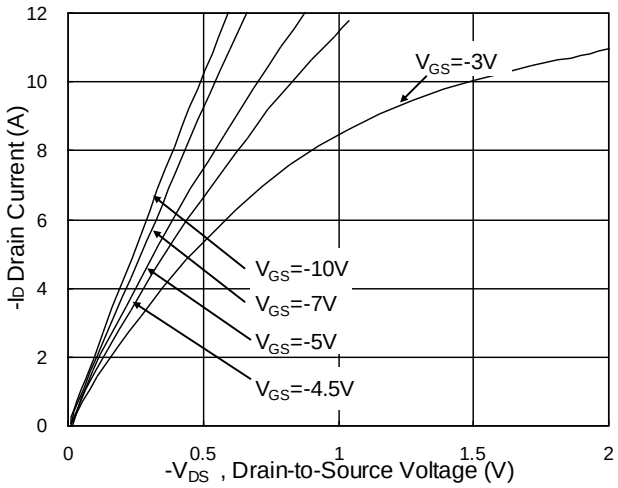


Fig.1 Typical Output Characteristics

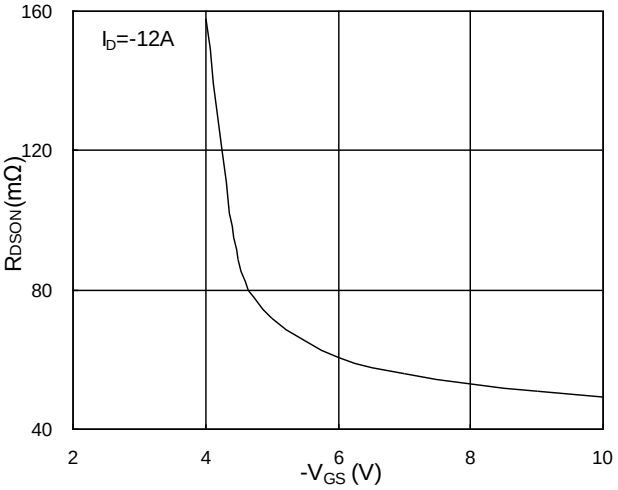


Fig.2 On-Resistance v.s Gate-Source

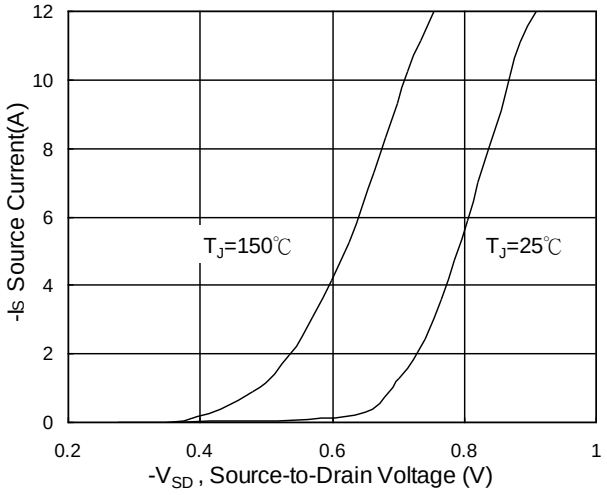


Fig.3 Forward Characteristics of Reverse

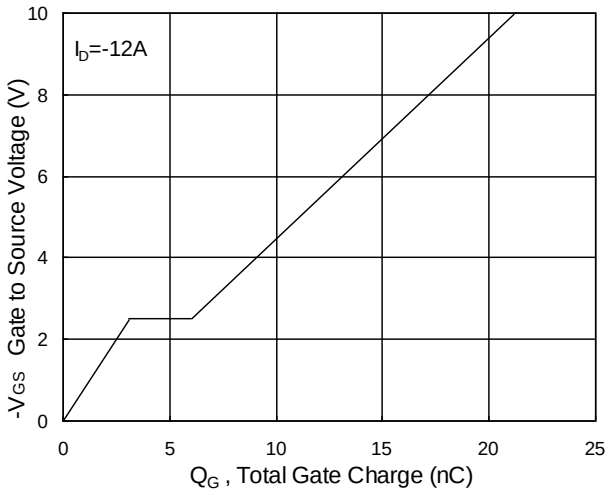


Fig.4 Gate-Charge Characteristics

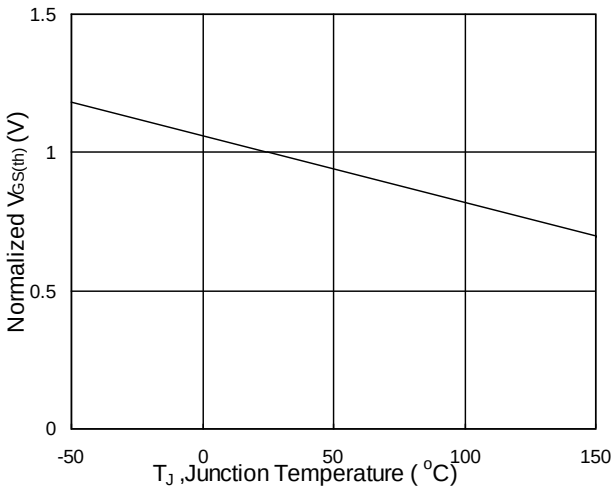


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

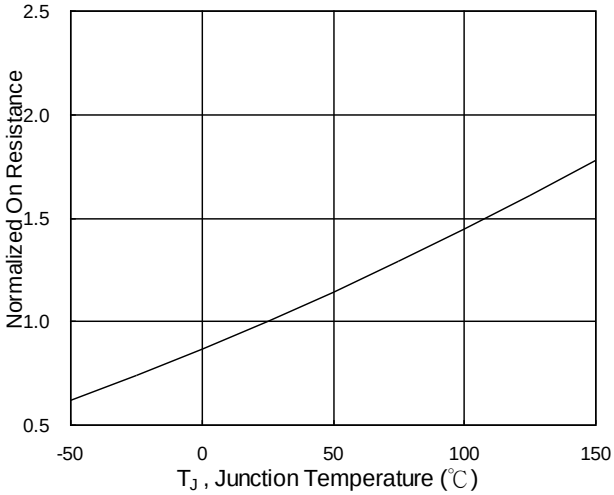


Fig.6 Normalized R_{DSON} v.s T_J

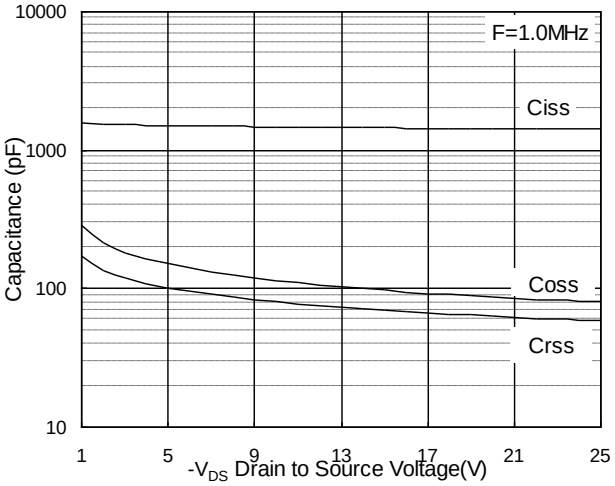


Fig.7 Capacitance

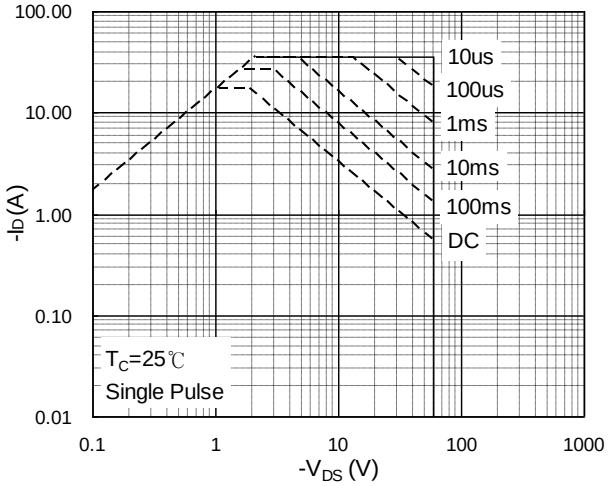


Fig.8 Safe Operating Area

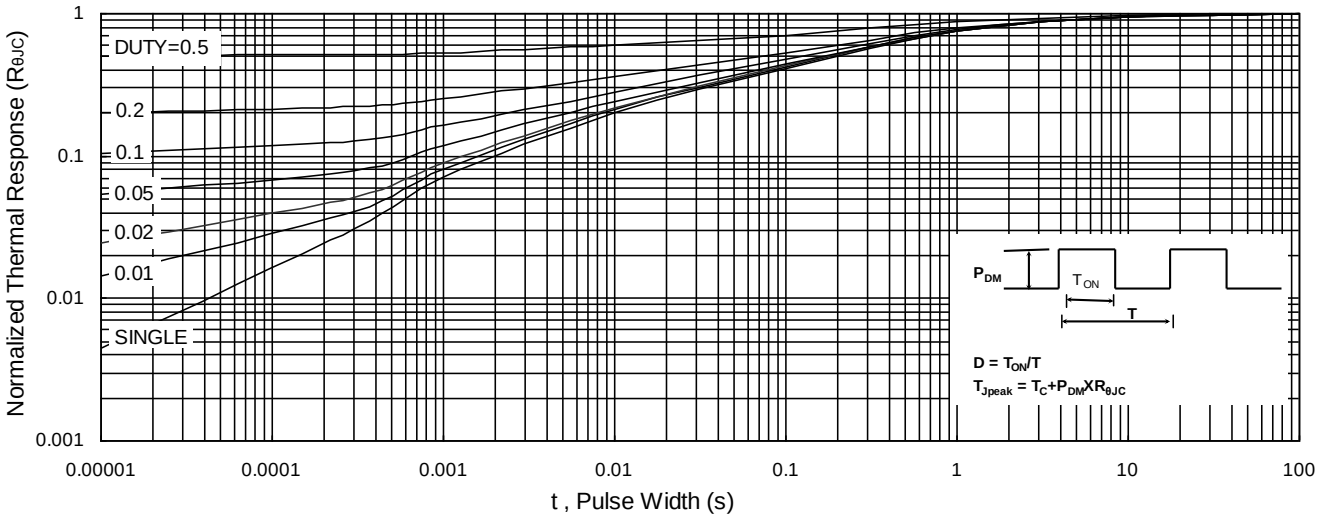


Fig.9 Normalized Maximum Transient Thermal Impedance

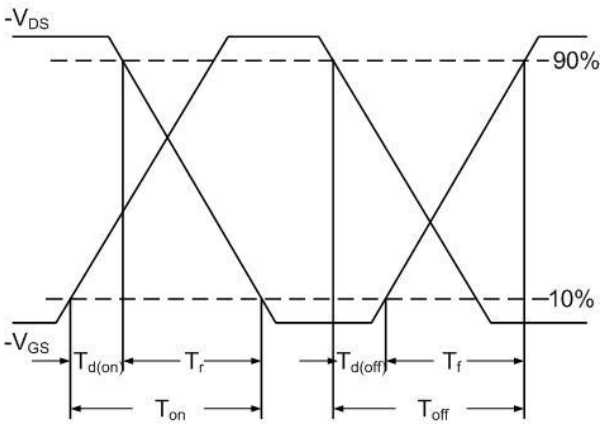


Fig.10 Switching Time Waveform

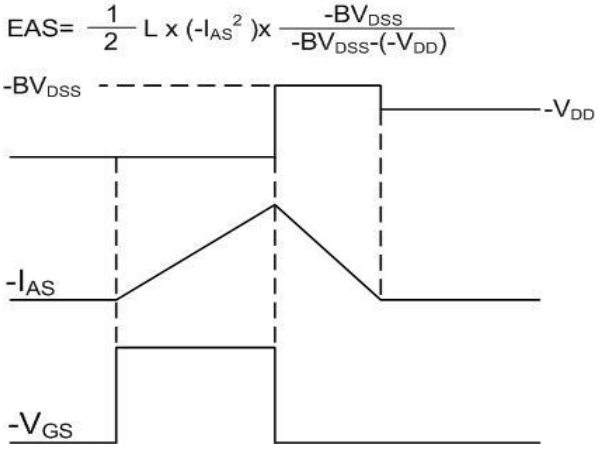
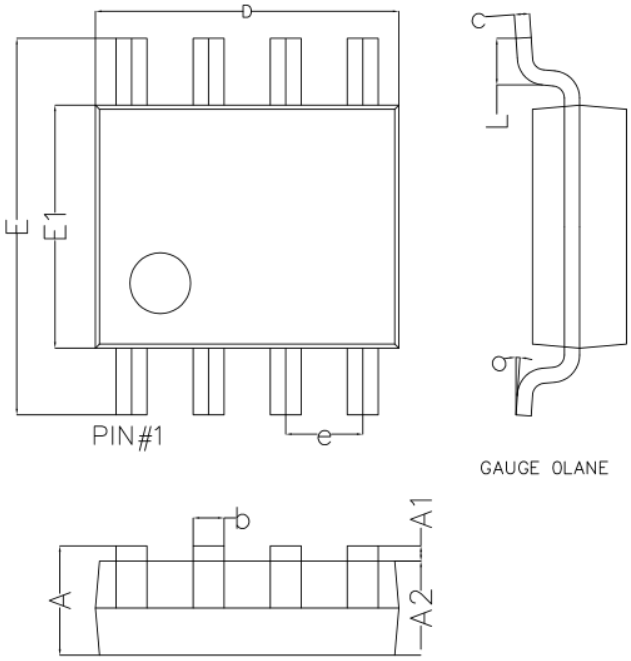


Fig.11 Unclamped Inductive Waveform

S0P8 Package outline



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	5.800	6.000	6.200
E1	3.800	3.900	4.000
L	0.400	0.835	1.2700
θ	0°	4°	8°

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